



60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	1.6mΩ @ V _{GS} = 10V	225A
607	2.8mΩ @ V _{GS} = 4.5V	180A

Features

- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

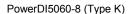
Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

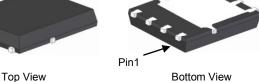
- **Engine Management Systems**
- **Body Control Electronics**
- DC-DC Converters

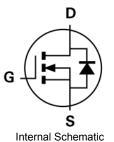
Mechanical Data

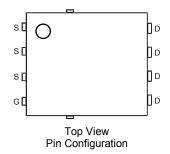
- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)











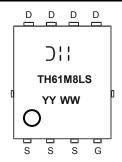
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH61M8LPS-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



⊃¦¦= Manufacturer's Marking TH61M8LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 21 = 2021) WW = Week (01 to 53)



Maximum Ratings (@ T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Prain Current V = 40V (Note 6)	T _C = +25°C	· I _D	225	- A
Continuous Drain Current, V _{GS} = 10V (Note 6)	T _C = +100°C		160	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	900	Α	
Maximum Continuous Body Diode Forward Current (Note 6) $T_C = +25^{\circ}C$		Is	225	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	900	Α	
Avalanche Current, L = 1mH		I _{AS}	34.8	Α
Avalanche Energy, L = 1mH		E _{AS}	605	mJ

Thermal Characteristics (@ T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	46	°C/W	
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	187.5	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	0.8	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@ T_C = +25°C, unless otherwise specified.)

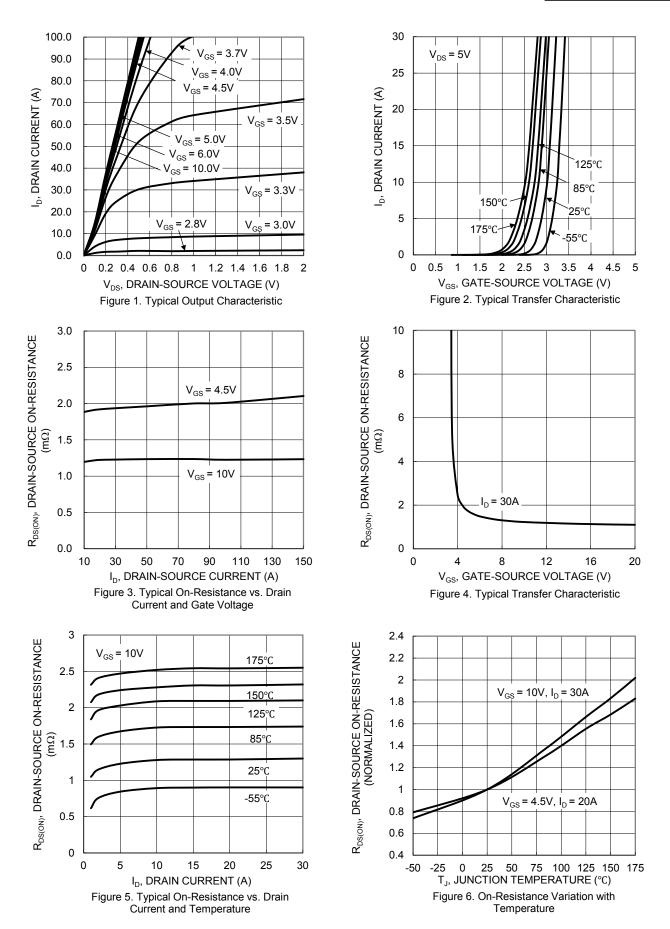
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}			±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 7)						•	
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	1.2	1.6	mΩ	V _{GS} = 10V, I _D = 30A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.9	2.8	11122	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	V _{GS} = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 8)		•				•	
Input Capacitance	C _{iss}	_	8320	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	2298	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	157	_		I - IIVIAZ	
Gate Resistance	Rg	_	3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	53.3	_		V 20V I 20A	
Total Gate Charge (V _{GS} = 10V)	Qg	_	115.5	_	nC		
Gate-Source Charge	Q_{gs}	_	27.8	_	110	$V_{DS} = 30V, I_{D} = 30A$	
Gate-Drain Charge	Q_{gd}	_	16.5	_			
Turn-On Delay Time	t _{D(ON)}	_	10.3	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 30A, R_{g} = 3\Omega$	
Turn-On Rise Time	t _R	_	23.9	_			
Turn-Off Delay Time	t _{D(OFF)}	_	108.3	_	ns		
Turn-Off Fall Time	t _F	_	51.7	_			
Body Diode Reverse Recovery Time	t _{RR}	_	64	_	ns	1 - 204 - 4:/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	124	_	nC	$I_F = 30A$, di/dt = 100A/ μ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

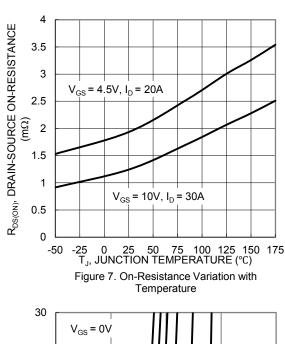
Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.

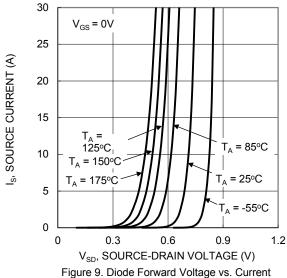
8. Guaranteed by design. Not subject to product testing.

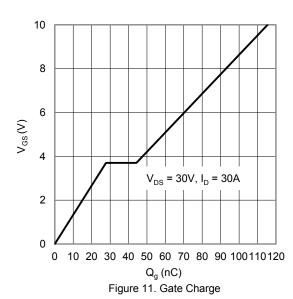












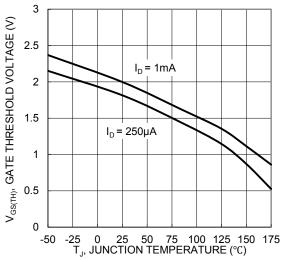


Figure 8. Gate Threshold Variation vs. Junction Temperature

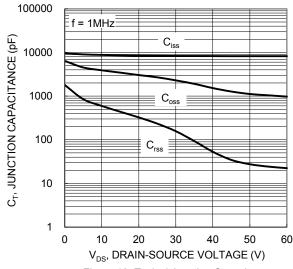


Figure 10. Typical Junction Capacitance

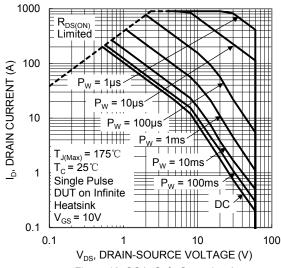


Figure 12. SOA, Safe Operation Area



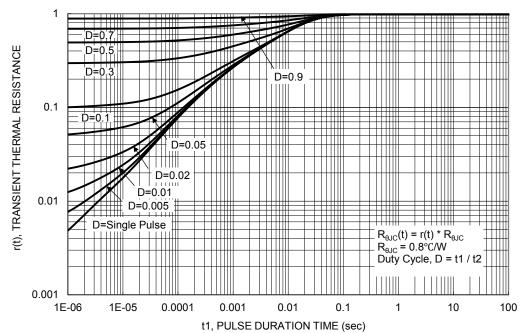


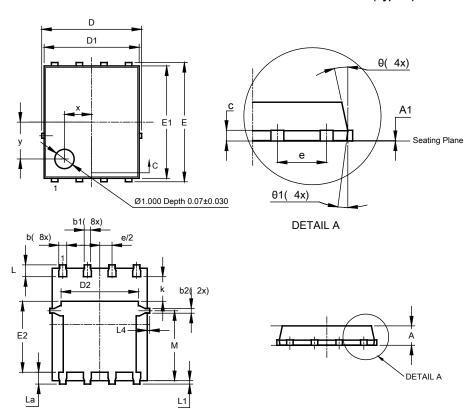
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)

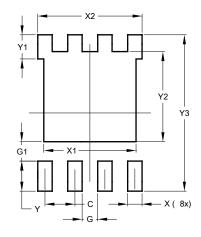


PowerDI5060-8 (Type K)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0	\sim		
D1	4.85	4.95	4.90		
D2	1	-	3.98		
Е	6	.15 BS0	\sim		
E1	5.75	5.85	5.80		
E2	3.56	3.725	3.66		
е	1	1.27BSC			
k	1	-	1.27		
L	0.51	0.71	0.61		
La	0.51	0.675	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
M	I 3.50 3.71		3.605		
X			1.400		
у			1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value		
Dilliensions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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